

a first plurality of spaced-apart conductors disposed at a first height above the substrate in a first direction; and

a second plurality of spaced-apart rail-stacks disposed above the first height in a second direction different from the first direction, each rail-stack including a semiconductor film of a first conductivity type in contact with said first plurality of spaced-apart conductors, a local charge storage film disposed above the semiconductor film and a conductive film disposed above the local charge storage film,

wherein the at least one driver circuit is not located in a bulk monocrystalline silicon substrate.

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cont. Please add the following new claims:

69. (New) A nonvolatile memory array, comprising:
an array of nonvolatile memory devices;
a silicon on insulator substrate; and
at least one memory driver circuit located in the silicon on insulator substrate.
 70. (New) The nonvolatile memory array of claim 1, wherein the nonvolatile memory devices are transistors each comprising a charge storage medium.
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